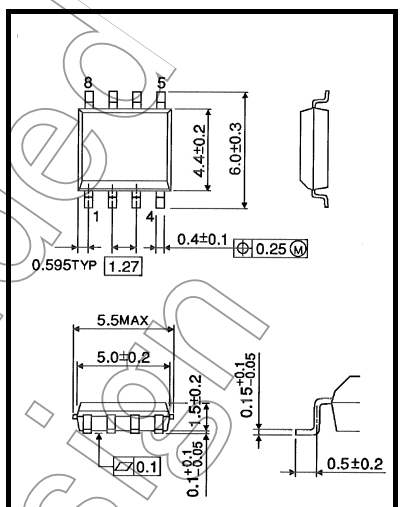
TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSV)

TPC8119

Lithium-Ion Battery Applications
Load switch Applications
Notebook PC Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance: $R_{DS\ (ON)}$ = 10 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 24 S (typ.)
- Low leakage current: I_{DSS} = −10 μA (max) (V_{DS} = −30 V)
- Enhancement mode: V_{th} = −0.8 to −2.0 V (V_{DS} = −10 V, I_D = −1 mA)

Unit: mm



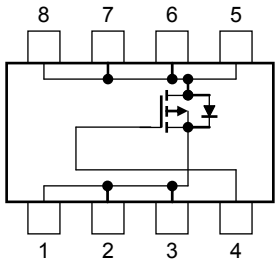
JEDEC	—
JEITA	—
TOSHIBA	2-6J1B

Weight: 0.080 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	−30	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	−30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	−10	A
	Pulse (Note 1)	I_{DP}	−40	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.9	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.0	W
Single pulse avalanche energy (Note 3)		E_{AS}	67	mJ
Avalanche current		I_{AR}	−10	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	0.030	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

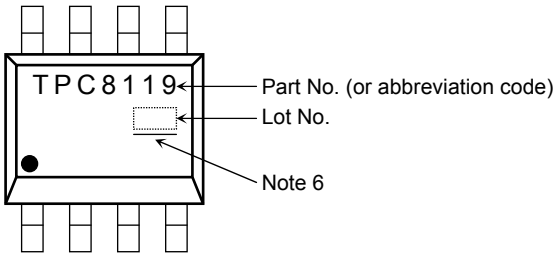
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Please handle with care.

Thermal Characteristics

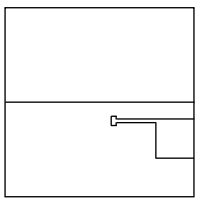
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	125	°C/W

Marking (Note 5)



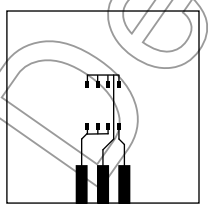
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

(a)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

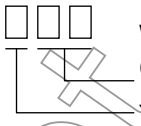
(b)

Note 3: V_{DD} = −24 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_G = 25 Ω, I_{AR} = −10 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on the lower left of the marking indicates Pin 1.

* Weekly code: (Three digits)



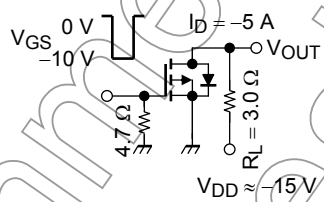
Week of manufacture
(01 for first week of year, continuing up to 52 or 53)

Year of manufacture
(The last digit of the calendar year)

Note 6: A line under a Lot No. identifies the indication of product Labels.
Not underlined: [[Pb]]/INCLUDES > MCV
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	—	—	±100	nA
Drain cut-off current		I_{DSS}	V_{DS} = −30 V, V_{GS} = 0 V	—	—	−10	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −10 mA, V_{GS} = 0 V	−30	—	—	V
		$V_{(BR)\ DSX}$	I_D = −10 mA, V_{GS} = 20 V	−13	—	—	
Gate threshold voltage		V_{th}	V_{DS} = −10 V, I_D = −1 mA	−0.8	—	−2.0	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = −4 V, I_D = −5 A	—	20	28	mΩ
			V_{GS} = −10 V, I_D = −5 A	—	10	13	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −5 A	12	24	—	S
Input capacitance		C_{iss}	V_{DS} = −10 V, V_{GS} = 0 V, f = 1 MHz	—	1560	—	pF
Reverse transfer capacitance		C_{rss}		—	350	—	
Output capacitance		C_{oss}		—	475	—	
Switching time	Rise time	t_r		—	8	—	ns
	Turn-on time	t_{on}		—	16	—	
	Fall time	t_f		—	55	—	
	Turn-off time	t_{off}		—	145	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≈ −24 V, V_{GS} = −10 V, I_D = −10 A	—	40	—	nC
Gate-source charge 1		Q_{gs1}		—	5	—	
Gate-drain (“miller”) charge		Q_{gd}		—	13	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	−40	A
Forward voltage (diode)		V_{DSF}	I_{DR} = −10 A, V_{GS} = 0 V	—	—	1.2	V